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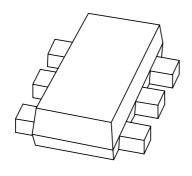
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Team Nexperia

# DISCRETE SEMICONDUCTORS

# DATA SHEET



PBSS5240V 40 V low V<sub>CEsat</sub> PNP transistor

Product data sheet 2003 Jan 30



# 40 V low V<sub>CEsat</sub> PNP transistor

#### PBSS5240V

#### **FEATURES**

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (hFE) at high IC
- High efficiency leading to reduced heat generation
- Reduced printed-circuit board area requirements.

#### **APPLICATIONS**

- Power management:
  - DC-DC converter
  - Supply line switching
  - Battery charger
  - LCD back lighting.
- · Peripheral driver:
  - Driver in low supply voltage applications (e.g. lamps, LEDs)
  - Inductive load drivers (e.g. relay, buzzers and motors).

#### **DESCRIPTION**

PNP transistor providing low  $V_{CEsat}$  and high current capability in a SOT666 plastic package. NPN complement: PBSS4240V.

#### **MARKING**

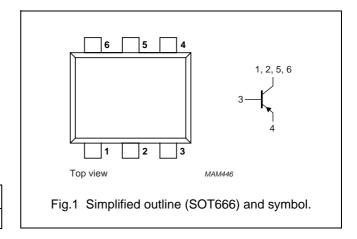
TYPE NUMBER	MARKING CODE		
PBSS5240V	52		

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage		V
I <sub>C</sub> collector current (DC)		-1.8	Α
I <sub>CRP</sub> peak collector current		-2	Α
R <sub>CEsat</sub> equivalent on-resistance		<250	mΩ

#### **PINNING**

PIN	DESCRIPTION	
1	collector	
2	collector	
3	base	
4	emitter	
5	collector	
6	collector	



## 40 V low V<sub>CEsat</sub> PNP transistor

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#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)	note 1	_	-1.8	А
I <sub>CRP</sub>	peak repetitive collector current	note 2	_	-2	А
I <sub>CM</sub>	peak collector current		_	-3	А
I <sub>B</sub> base current (DC)			_	-300	mA
I <sub>BM</sub>	peak base current		_	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 3	_	300	mW
		T <sub>amb</sub> ≤ 25 °C; note 4	_	500	mW
		T <sub>amb</sub> ≤ 25 °C; note 1	_	900	mW
		T <sub>amb</sub> ≤ 25 °C; notes 2 and 3	_	1.2	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### **Notes**

- 1. Device mounted on a ceramic circuit board, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- 2. Operated under pulsed conditions: duty cycle  $\delta \leq$  20%, pulse width  $t_p \leq$  30 ms.
- 3. Device mounted on a printed-circuit board, single-sided copper, tinplated, standard footprint.
- 4. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to	note 1	410	K/W
	ambient	note 2	215	K/W
		note 3	140	K/W
		notes 1 and 4	110	K/W

#### **Notes**

- 1. Device mounted on a printed-circuit board, single-sided copper, tinplated, standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.
- 3. Device mounted on a ceramic circuit board, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- 4. Operated under pulsed conditions: duty cycle  $\delta \leq$  20%, pulse width  $t_p \leq$  30 ms.

#### Soldering

The only recommended soldering method is reflow soldering.

# 40 V low $V_{\text{CEsat}}$ PNP transistor

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#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

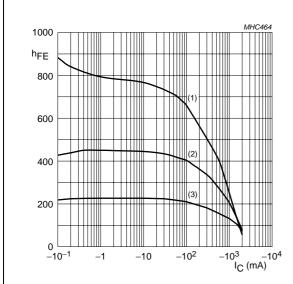
SYMBOL	PARAMETER	PARAMETER CONDITIONS		TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -40 \text{ V}; I_E = 0$	_	_	-100	nA
		V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0; T <sub>amb</sub> = 150 °C	_	_	-50	μΑ
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	300	_	_	
		$V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}$	300	_	800	
		$V_{CE} = -5 \text{ V}; I_{C} = -500 \text{ mA}$	250	_	-	
		$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$	160	_	_	
		$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ A}; \text{ note 1}$	50	_	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -100 \text{ mA}; I_B = -1 \text{ mA}$	_	-80	-120	mV
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	-	-100	-145	mV
		$I_C = -1 \text{ A}$ ; $I_B = -100 \text{ mA}$ ; note 1	_	-180	-250	mV
		$I_C = -2 \text{ A}; I_B = -200 \text{ mA}$	_	-370	-530	mV
R <sub>CEsat</sub>	equivalent on-resistance	$I_C = -1 \text{ A}$ ; $I_B = -100 \text{ mA}$ ; note 1	-	180	<250	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -1 \text{ A}; I_B = -100 \text{ mA}$	-	_	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$	_	_	-1	V
f <sub>T</sub>	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 100 MHz	150	_	_	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	-	12	pF

#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

# 40 V low V<sub>CEsat</sub> PNP transistor

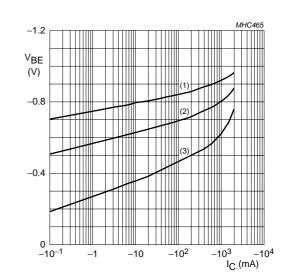
# PBSS5240V



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

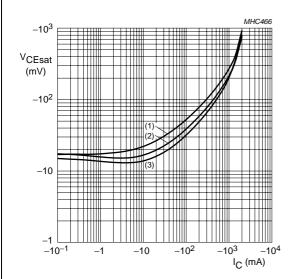
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2) T<sub>amb</sub> = 25 °C.
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

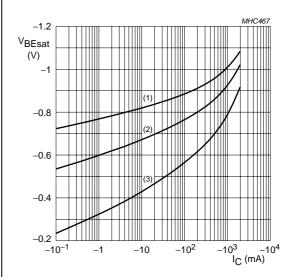
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



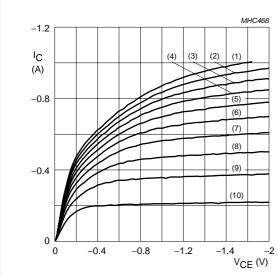
 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

# 40 V low V<sub>CEsat</sub> PNP transistor

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 $T_{amb}$  = 25 °C.

(1)  $I_B = -7 \text{ mA}$ .

(5)  $I_B = -4.2 \text{ mA}.$ 

(9)  $I_B = -1.4 \text{ mA}.$ 

(2)  $I_B = -6.3 \text{ mA}.$ 

(6)  $I_B = -3.5 \text{ mA}.$ 

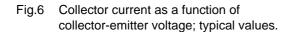
(10)  $I_B = -0.7 \text{ mA}.$ 

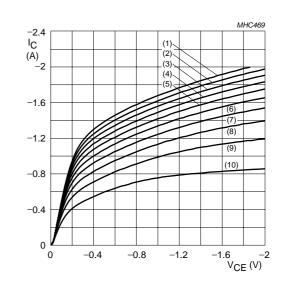
(3)  $I_B = -5.6 \text{ mA}.$ 

(7)  $I_B = -2.8 \text{ mA}.$ 

(4)  $I_B = -4.9 \text{ mA}$ .

(8)  $I_B = -2.1 \text{ mA}.$ 





 $T_{amb}$  = 25 °C.

(1)  $I_B = -50 \text{ mA}.$ 

(5)  $I_B = -30 \text{ mA}.$ 

(9)  $I_B = -10 \text{ mA}.$ 

(2)  $I_B = -45 \text{ mA}.$ 

(6)  $I_B = -25 \text{ mA}.$ 

(10)  $I_B = -5 \text{ mA}$ .

(3)  $I_B = -40 \text{ mA}$ . (4)  $I_B = -35 \text{ mA}$ . (7)  $I_B = -20 \text{ mA}.$ (8)  $I_B = -15 \text{ mA}.$ 

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

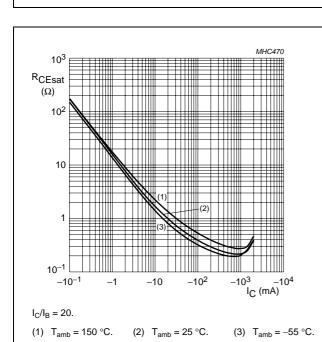


Fig.8 Collector-emitter equivalent on-resistance as a function of collector current; typical values.

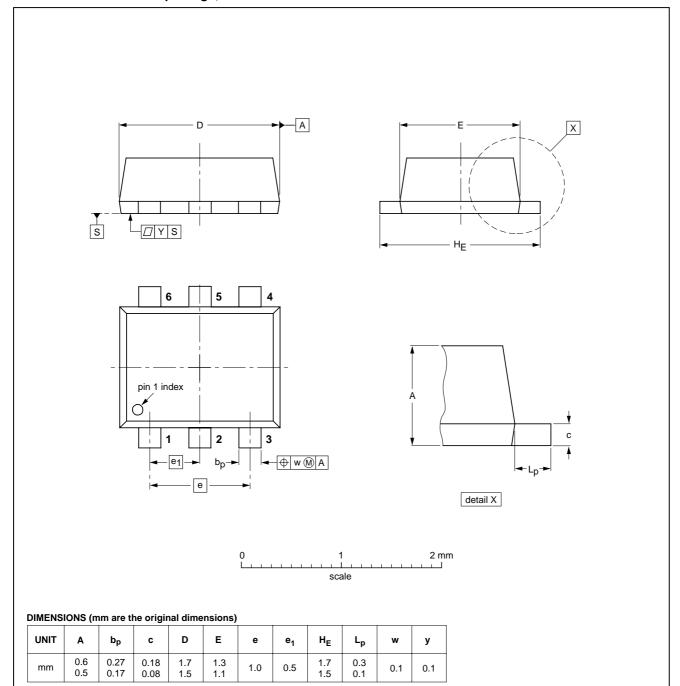
# 40 V low V<sub>CEsat</sub> PNP transistor

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

**SOT666** 



OUTLINE	REFERENCES			EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>-01-01-04</del> 01-08-27

### 40 V low V<sub>CEsat</sub> PNP transistor

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DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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